

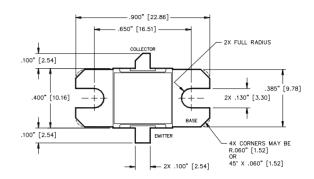
# Radar Pulsed Power Transistor 30W, 3.1-3.4 GHz, 1µs Pulse, 10% Duty

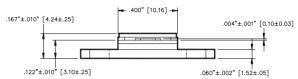
Rev. V1

#### **Features**

- · NPN silicon microwave power transistors
- Common base configuration
- Broadband Class C operation
- · High efficiency inter-digitized geometry
- Diffused emitter ballasting resistors
- Gold metallization system
- Internal input and output impedance matching
- Hermetic metal/ceramic package
- · RoHS compliant

### **Outline Drawing**





UNLESS OTHERWISE NOTED, TOLERANCES ARE INCHES  $\pm .005$ " [MILLIMETERS  $\pm 0.13$ MM]

### Absolute Maximum Ratings at 25°C

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	$V_{CES}$	65	V
Emitter-Base Voltage	$V_{EBO}$	3.0	V
Collector Current (Peak)	Ic	3.6	Α
Power Dissipation @ +25°C	P <sub>TOT</sub>	350	W
Storage Temperature	$T_{STG}$	-65 to +200	°C
Junction Temperature	TJ	200	°C

## Electrical Specifications: T<sub>C</sub> = 25 ± 5°C (Room Ambient)

Parameter	Test Conditions	Frequency	Symbol	Min	Max	Units
Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA		$BV_CES$	65	-	V
Collector-Emitter Leakage Current	V <sub>CE</sub> = 40V		I <sub>CES</sub>	-	1.5	mA
Thermal Resistance	Vcc = 36V, Pout = 30W	F = 3.1, 3.25, 3.4 GHz	R <sub>TH(JC)</sub>	-	0.5	°C/W
Input Power	Vcc = 36V, Pout = 30W	F = 3.1, 3.25, 3.4 GHz	P <sub>IN</sub>	-	5.33	W
Power Gain	Vcc = 36V, Pout = 30W	F = 3.1, 3.25, 3.4 GHz	G <sub>P</sub>	7.5	-	dB
Collector Efficiency	Vcc = 36V, Pout = 30W	F = 3.1, 3.25, 3.4 GHz	ης	35	-	%
Input Return Loss	Vcc = 36V, Pout = 30W	F = 3.1, 3.25, 3.4 GHz	RL	-	-6	dB
Load Mismatch Tolerance	Vcc = 36V, Pout = 30W	F = 3.25 GHz	VSWR-T	-	2:1	-

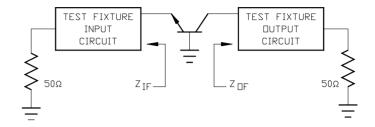


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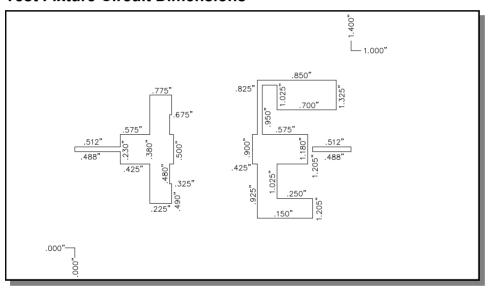
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### **RF Test Fixture Impedance**

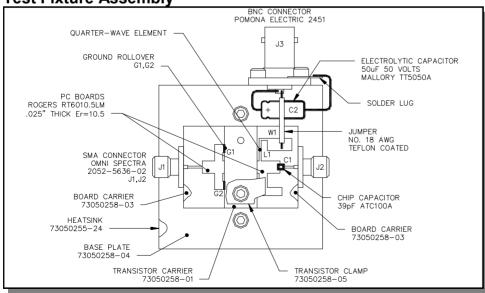
F (GHz)	Z <sub>IF</sub> (Ω)	Z <sub>OF</sub> (Ω)
3.10	16.0 + j5.0	19.0 + j3.0
3.25	14.5 + j2.0	15.5 - j2.0
3.40	11.5 + j0.0	10.0 - j3.5



### **Test Fixture Circuit Dimensions**



**Test Fixture Assembly** 



# PH3134-30S



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